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FERAM CELL WITH INTERNAL OXYGEN SOURCE
AND METHOD OF OXYGEN RELEASE

ABSTRACT OF THE DISCLOSURE

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An integrated ferroelectric/CMOS structure which comprises at least a ferroelectric material, a pair of electrodes in contact with opposite surfaces of the ferroelectric material, where the electrodes do not decompose at

15 deposition or annealing, and an oxygen source layer in contact with at least one of said electrodes, said oxygen source layer being a metal oxide which at least partially decomposes during deposition and/or subsequent processing is provided as well as a method of fabricating the same.